20V 6.8A N-Channel Enhancement Mode Power MOSFET

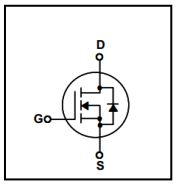
General Description

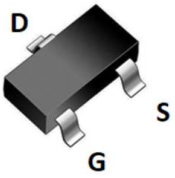
This Power MOSFET has been developed using advanced trench process, which is specifically designed to minimize input capacitance and gate charge. This renders the device suitable for use as primary switch in advanced high-efficiency isolated DC-DC converters for telecom and computer applications, and applications with low gate charge driving requirements.

FEATURES

- RDSON≤21mΩ @Vgs=4.5V, Id=4A
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

SYMBOL





SOT-23 top view

ASSEMBLY MESSAGE

Product Name	Marking	Package	Packaging
BXT210N02M	2312	SOT-23	Reel

ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

Parameter		Symbol	Rating	Unit
			SOT-23	
Drain-Source Voltage		V_{DSS}	20	V
Drain Current	Continuous (T_C = 25°C)	I_D	6.8	A
	Continuous (T_C = 100°C)		4.4	A
Drain Current	Pulsed (Note1)	I_{DM}	27.2	A
Gate-Source Voltage		V_{GSS}	±12	V
Power Dissipation	T_C =25°C	P_D	1.6	W
Maximum Junction Temperature		T_J	150	°C
Storage Temperature Range		T_{STG}	-55 to 150	°C

Note： 1. Repetitive Rating: Pulse width limited by maximum junction temperature